

www.vishay.com

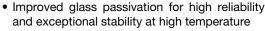
## Vishay Semiconductors

# Medium Power Phase Control Thyristors (Stud Version), 22 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	22 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V				
$V_{TM}$	1.70 V				
I <sub>GT</sub>	60 mA				
T <sub>J</sub>	-65 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration	Single SCR				

#### **FEATURES**





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		22	Α		
$I_{T(AV)}$	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		35	Α		
I <sub>TSM</sub>	50 Hz	400	۸		
	60 Hz	420	A		
l <sup>2</sup> t	50 Hz	793	— A <sup>2</sup> s		
	60 Hz	724	A-s		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
tq	Typical	110	μs		
T <sub>J</sub>		-65 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-22RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### **Notes**

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

<sup>(2)</sup> For voltage pulses with  $t_p \le 5$  ms



PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS
Maximum average on-state current	,	180° sinusoidal conduction		22	Α	
at case temperature	I <sub>T(AV)</sub>	160 Sinusc	dai conduction		85	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				35	Α
		t = 10 ms	No voltage		400	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		420	1 ,
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		335	- A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	355	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage		793	- A <sup>2</sup> s
	l <sup>2</sup> t	t = 8.3 ms	reapplied		724	
		t = 10 ms	100 % V <sub>RRM</sub>		560	
		t = 8.3 ms	reapplied		515	
Maximum $I^2 \sqrt{t}$ for fusing	I <sup>2</sup> √t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		7930	A²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < $I$ < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		0.83	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$f_{0}$ ), $T_{J} = T_{J}$ maxim	num	0.95	] v
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		14.9	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.4	1115.2	
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 70 A, T <sub>J</sub> = 25 °C		1.70	V	
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada aunnis 6	V registive lead	130	
Latching current	ΙL	$I_{\rm J} = 25^{\circ} \rm C$	$T_J = 25$ °C, anode supply 6 V, resistive load		200	- mA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$				
Maximum rate of rise	$V_{DRM} \le 800 \text{ V}$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ Gate pulse = 20 V, 15 $\Omega$ , $t_D = 6 \mu s$ , $t_r = 0.1 \mu s$ maximum	180	A/μs
of turned-on current	$V_{DRM} \le 1000 \text{ V}$	ui/ut	$I_{TM} = (2 \text{ x rated dI/dt}) \text{ A}$	160	
	$V_{DRM} \le 1600 \text{ V}$			150	
Typical turn-on time		t <sub>gt</sub>	$T_J = 25$ °C, at rated $V_{DRM}/V_{RRM}$ , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \ \mu s$ , $dI/dt = -10 \ A/\mu s$	4	μs
Typical turn-off time		t <sub>q</sub>	$T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	μ

#### Note

•  $t_q = 10 \mu s$  up to 600 V,  $t_q = 30 \mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 100 % rated V <sub>DRM</sub>	100	V/µs
of off-state voltage	uv/ut	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	300 (1)	ν/μδ

#### Note

(1) Available with:  $dV/dt = 1000 V/\mu s$ , to complete code add S90 i.e. 22RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$	$T_{.1} = T_{.1}$ maximum		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>	I J = I J Maximum		2.0	VV
Maximum peak positive gate current	I <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
		T <sub>J</sub> = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units	90	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		60	mA
		T <sub>J</sub> = 125 °C		35	
	V <sub>GT</sub>	T <sub>J</sub> = - 65 °C		3.0	V
DC gate voltage required to trigger		T <sub>J</sub> = 25 °C	6 V anode to cathode applied	2.0	
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		2.0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +125		°C
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation 0.86		14004	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased 0.35		35	K/W
			TO NUT	TO DEVICE	
			20 (27.5)	25	lbf ⋅ in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m
		(von aznazioa amosas)	2.3 (3.1)	2.8	N · m
Approximate weight			1	4	g
Approximate weight			0.	49	OZ.
Case style		See dimensions - link at the end of datasheet	t TO-48 (TO-208AA)		A)

△R <sub>thJC</sub> CONDUCTION	I			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15		
120°	0.25	0.25		
90°	0.31	0.34	$T_J = T_J$ maximum	K/W
60°	0.45	0.47		
30°	0.76	0.76		

### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

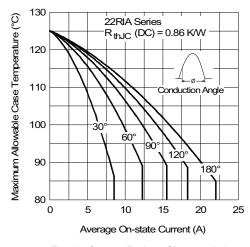


Fig. 1 - Current Ratings Characteristics

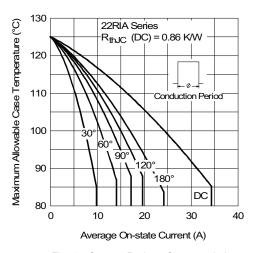


Fig. 1 - Current Ratings Characteristics

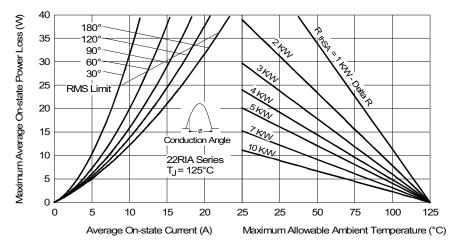


Fig. 2 - On-State Power Loss Characteristics

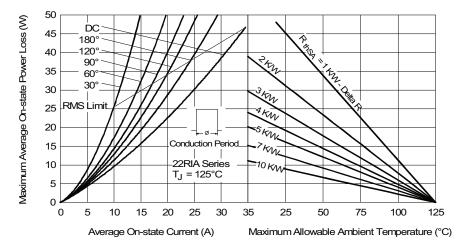


Fig. 3 - On-State Power Loss Characteristics

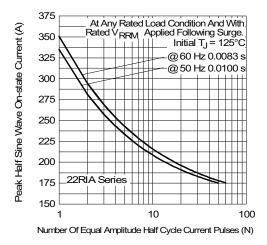


Fig. 4 - Maximum Non-Repetitive Surge Current

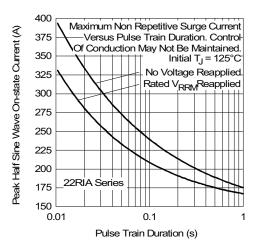


Fig. 5 - Maximum Non-Repetitive Surge Current

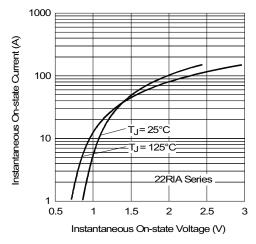


Fig. 6 - Forward Voltage Drop Characteristics

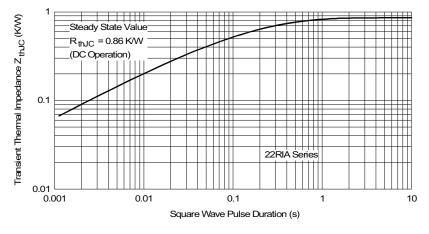


Fig. 7 - Thermal Impedance  $Z_{thJC}$  Characteristics

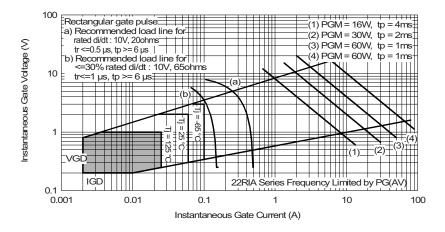
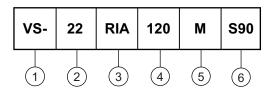


Fig. 8 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)

5 - None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A

M = stud base TO-48 (TO-208AA) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

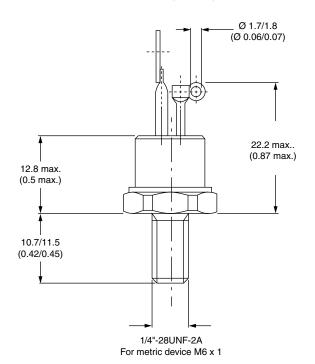
S90 = 1000 V/µs (special selection)

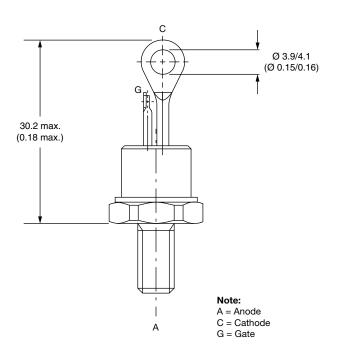
LINKS TO RELAT	TED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

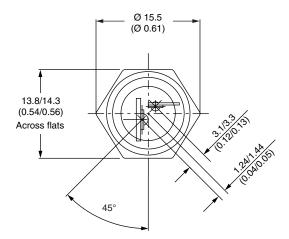


# TO-208AA (TO-48)

## **DIMENSIONS** in millimeters (inches)









## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## Vishay:

VS-22RIA10 VS-22RIA120 VS-22RIA20 VS-22RIA40 VS-22RIA60 VS-22RIA80 VS-22RIA100 VS-22RIA120S90